

## Silicon TVS Diode

- ESD / transient protection of data and power lines in low voltage applications according to: IEC61000-4-2 (ESD): ± 25 kV (air) 20 kV (contact) IEC61000-4-4 (EFT): 50 A / 2.5 kV (5/50 ns) IEC61000-4-5 (surge): 5.5 A / 66 W (8/20 μs)
- Small form factor (0402 inch): 1.0 x 0.6 x 0.4 mm<sup>3</sup>
- Uni-directional, working voltage up to 5.3 V
- Ultralow clamping voltage, protects against both positive and negative ESD strikes
- Ultralow dynamic resistance  $\textbf{0.27}\Omega$
- Very fast response time
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101

### Applications

- Digital interfaces (medium speed)
- Vcc protection
- Keypad, trackball protection, camera, displays in: mobile communications (smartphone, camera phone & added functions e.g. mobile TV)
- Digital consumer & computer electronics: laptops, PC, laserjet printer, photo printer, scanner, input devices (mouse, keyboard, remote control ...)
- Industrial: security systems, sensors, white goods.



### ESD5V3S1U-02LRH



Туре	Package	Configuration	Marking
ESD5V3S1U-02LRH	TSLP-2-17	1 line, uni-directional	E2





# **Maximum Ratings** at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit				
ESD air / contact discharge <sup>1)</sup>	V <sub>ESD</sub>	25 / 20	kV				
Peak pulse current ( $t_p = 8 / 20 \ \mu s$ ) <sup>2)</sup>	I <sub>pp</sub>	5.5	А				
Peak pulse power ( $t_p = 8 / 20 \ \mu s^{2}$ )	P <sub>pk</sub>	66	W				
Operating temperature range	T <sub>op</sub>	-55125	°C				
Storage temperature	T <sub>stg</sub>	-65150					

# **Electrical Characteristics** at $T_A = 25^{\circ}C$ , unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Characteristics					
Reverse working voltage	V <sub>RWM</sub>	-	-	5.3	V
Breakdown voltage	V <sub>(BR)</sub>	5.7	-	-	
<i>l</i> <sub>(BR)</sub> = 1 mA					
Reverse current	I <sub>R</sub>	-	-	0.1	μA
V <sub>R</sub> = 3.3 V					
Clamping voltage	V <sub>CL</sub>				V
$I_{\rm PP}$ = 1 A, $t_{\rm p}$ = 8/20 µs <sup>2)</sup>		-	7	9	
$I_{\rm PP}$ = 3.5 A, $t_{\rm p}$ = 8/20 µs <sup>2</sup> )		-	8	10	
$I_{\rm PP}$ = 5.5 A, $t_{\rm p}$ = 8/20 µs <sup>2</sup> )		-	9	11	
Forward clamping voltage	V <sub>FC</sub>				
$I_{\rm PP}$ = 1 A, $t_{\rm p}$ = 8/20 µs <sup>2)</sup>		-	1.2	2	
$I_{\rm PP}$ = 3.5 A, $t_{\rm p}$ = 8/20 µs <sup>2</sup> )		-	2	3	
$I_{\rm PP}$ = 5.5 A, $t_{\rm p}$ = 8/20 µs <sup>2</sup> )		-	2.5	3.5	
Diode capacitance	CT				pF
$V_{R} = 0 V, f = 1 MHz$		-	35	40	
V <sub>R</sub> = 2.5 V, <i>f</i> = 1 MHz		-	20	-	
Dynamic resistance <sup>3)</sup> ( $t_p = 30 \text{ ns}$ )	R <sub>D</sub>	-	0.27	-	Ω

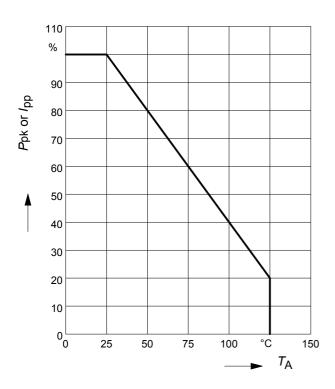
 $^{1}V_{\text{ESD}}$  according to IEC61000-4-2

 $^2\textit{I}_{pp}$  according to IEC61000-4-5

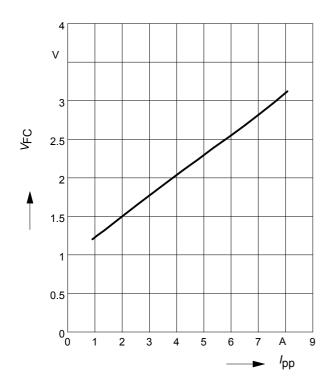
<sup>3</sup> according to TLP tests



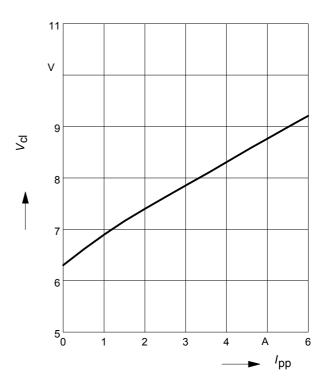
Power derating curve  $P_{pk} = f(T_A)$ 



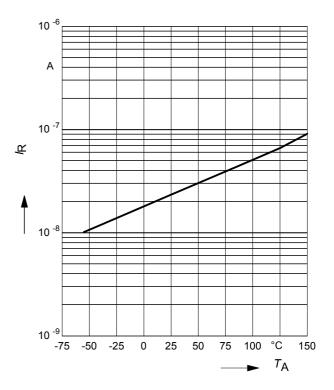
Forward clamping voltage  $V_{FC} = f(I_{PP})$  $t_p = 8 / 20 \ \mu s$ 



Clamping voltage,  $V_{cl} = f(I_{pp})$  $t_p = 8 / 20 \ \mu s$ 



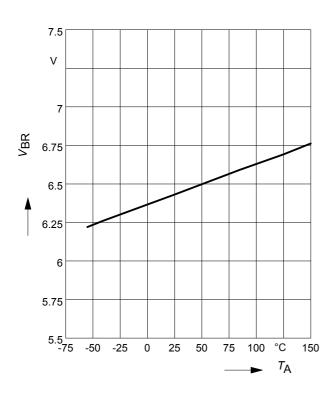
Reverse current  $I_R = f(T_A)$  $V_R = 3.3 V$ 





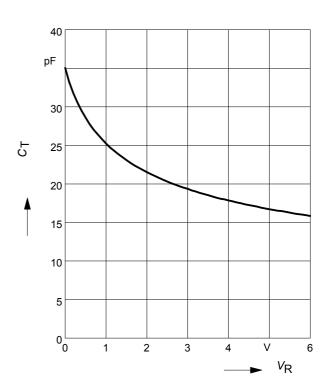
# Breakdown voltage $V_{BR} = f(T_A)$

*I*<sub>R</sub> = 1 mA



**Diode capacitance**  $C_{T} = f(V_{R})$ 

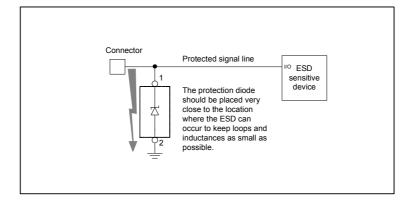
f = 1 MHz



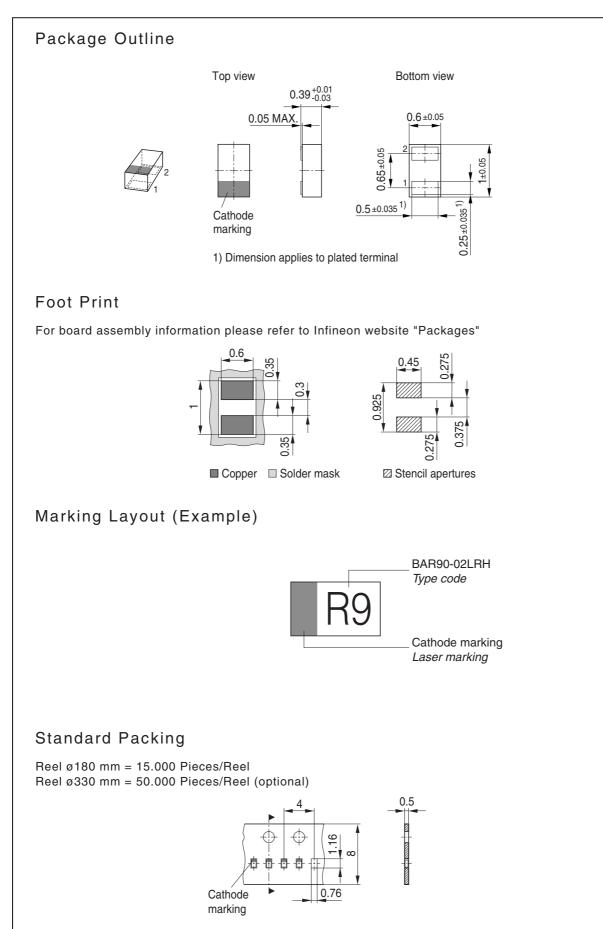


## Application example

single channel, uni-directional









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